

R-C Thermal Model Parameters

DESCRIPTION

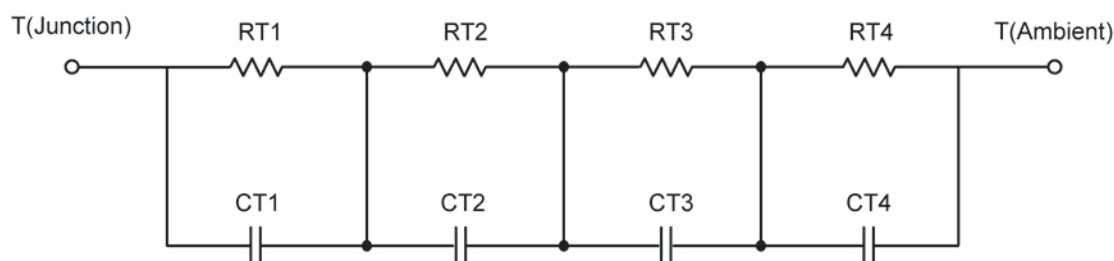
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

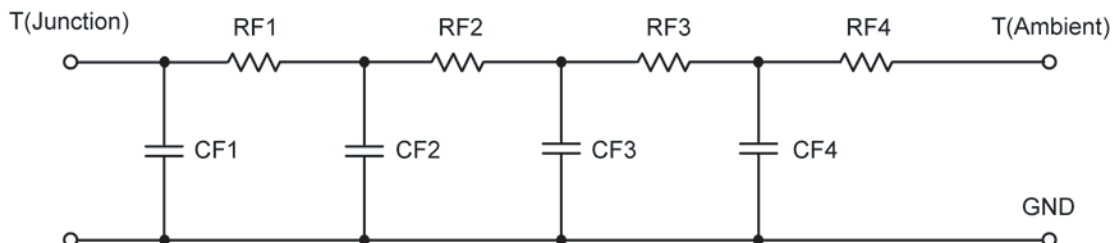
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	27.4179	N/A	10.8793
RT2	7.7888	N/A	3.1294
RT3	18.2397	N/A	8.5121
RT4	56.1996	N/A	7.4800
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	6.9455 m	N/A	3.7383 m
CT2	1.0952 m	N/A	487.9321 u
CT3	59.8102 m	N/A	23.5279 m
CT4	1.3314	N/A	20.5147 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	6.0609	N/A	3.4805
RF2	25.8785	N/A	10.4003
RF3	22.1016	N/A	10.8019
RF4	55.6703	N/A	5.3200
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	585.4437 μ	N/A	366.4125 μ
CF2	3.5347 m	N/A	2.2600 m
CF3	24.3746 m	N/A	1.3394 m
CF4	1.3064	N/A	38.5679 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

